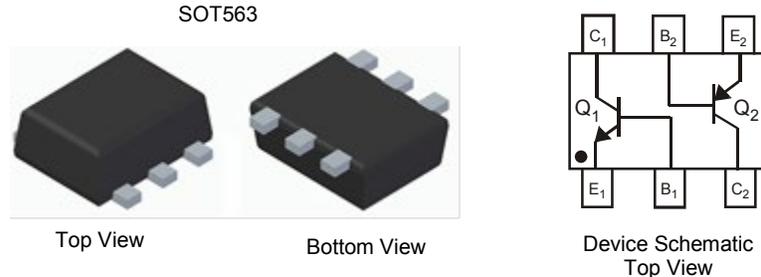


Features

- Epitaxial Die Construction
- Two Internally Isolated NPN/PNP Transistors in One Package
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**
- **An Automotive-Compliant Part Is Available Under Separate Datasheet ([BC847BVNQ](#))**

Mechanical Data

- Surface Mount Package
- Weight: 0.003 grams (Approximate)
- Max Soldering Temperature +260°C for 30 secs as per JEDEC J-STD-020
- Case Material – Molded Plastic, UL Flammability Rating 94V-0
- Terminals: Finish – Matte Tin Plated Leads, Solderable
- per MIL-STD-202, Method 208

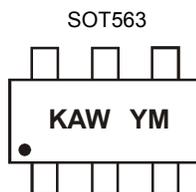


Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC847BVN-7	Standard	KAW	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



KAW = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: H = 2020)
 M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	H	I	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings: NPN, BC847B Type (Q₁) (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	I _C	100	mA
Peak Pulse Collector Current (single pulse)	I _{CM}	200	mA
Peak Pulse Emitter Current (single pulse)	I _{EM}	200	mA

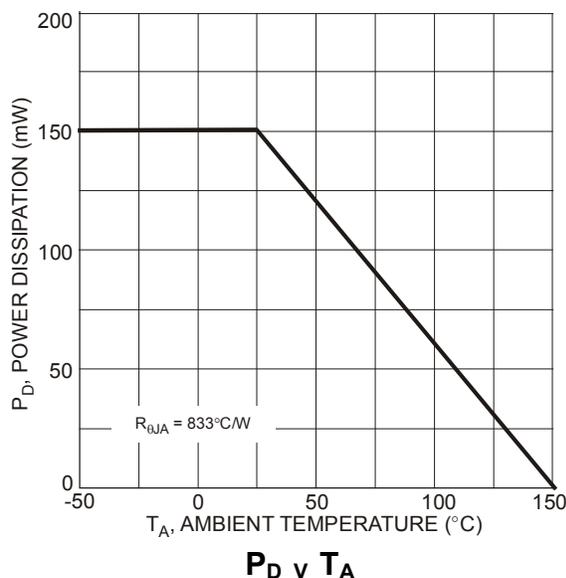
Maximum Ratings: PNP, BC857B Type (Q₂) (@ T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current	I _C	-100	mA
Peak Pulse Collector Current (single pulse)	I _{CM}	-200	mA
Peak Pulse Emitter Current (single pulse)	I _{EM}	-200	mA

Thermal Characteristics – Total Device (@ T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Total Device	P _D	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

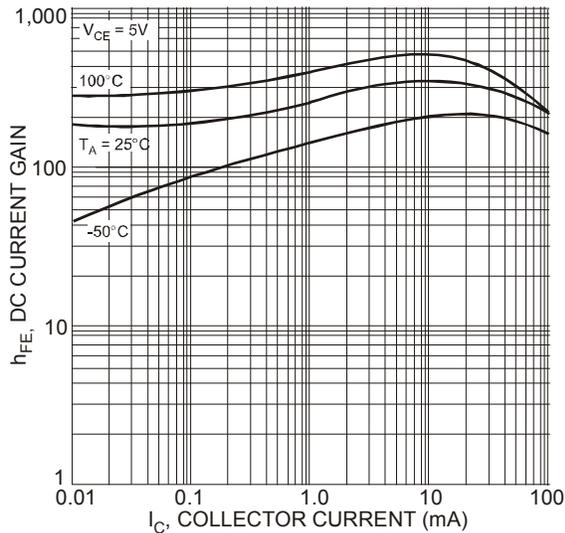
Note: 5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

Thermal Characteristics – Total Device


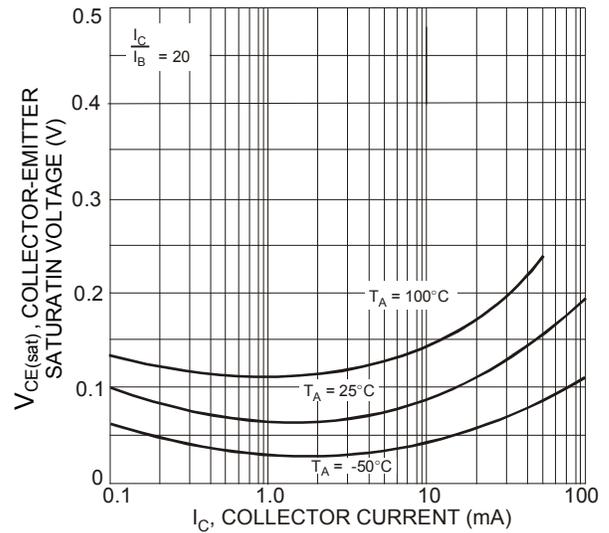
Electrical Characteristics: NPN, BC847B Type (Q₁) (@ T_A = +25°C unless otherwise specified.)

Characteristic (Note 6)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CB0}	50	—	—	V	I _C = 100μA, I _B = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	45	—	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	6	—	—	V	I _E = 100μA, I _C = 0
DC Current Gain	h _{FE}	200	290	450	—	V _{CE} = 5.0V, I _C = 2.0mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	90	250	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	700	—	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Voltage	V _{BE(on)}	580	660	700	mV	V _{CE} = 5.0V, I _C = 2.0mA V _{CE} = 5.0V, I _C = 10mA
Collector Cut Off Current	I _{CB0}	—	—	15	nA	V _{CB} = 30V
		—	—	5.0	μA	V _{CB} = 30V, T _A = +150°C
Transition Frequency	f _T	100	300	—	MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz
Collector-Base Capacitance	C _{cbo}	—	3.5	6.0	pF	V _{CB} = 10V, f = 1.0MHz

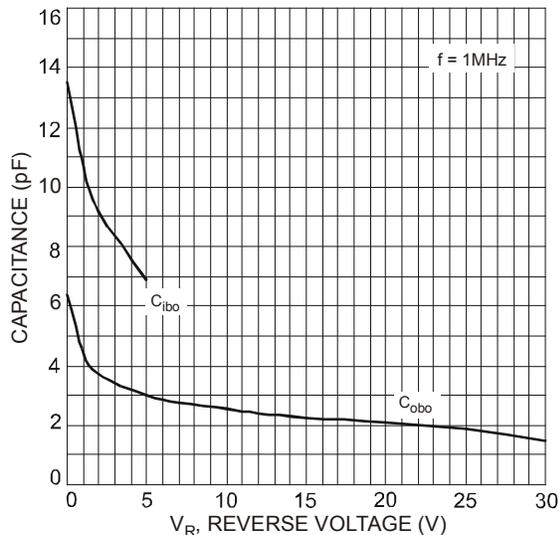
Note: 6. Short duration pulse test used to minimize self-heating effect.



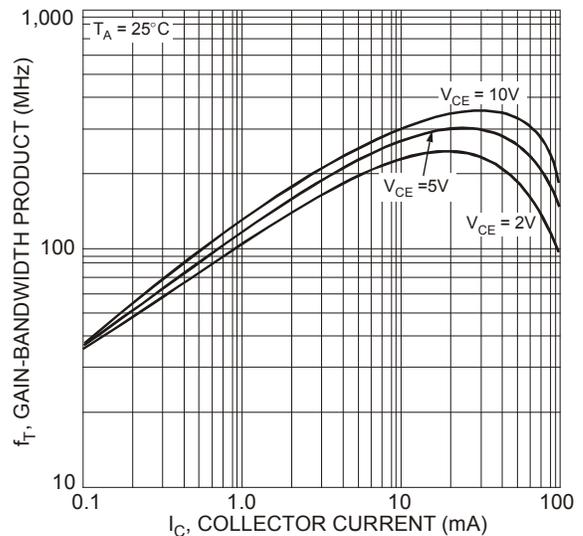
h_{FE} v I_C



V_{CE(sat)} v I_C



C v V_R

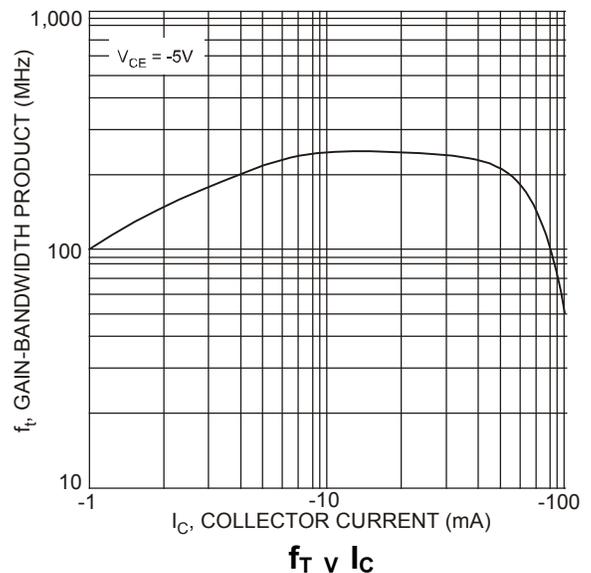
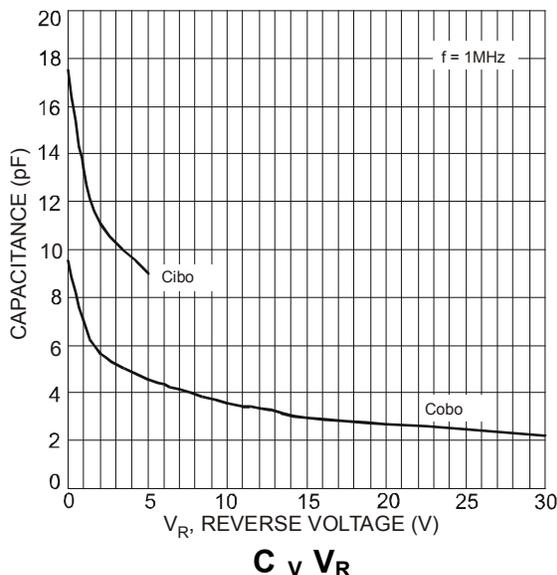
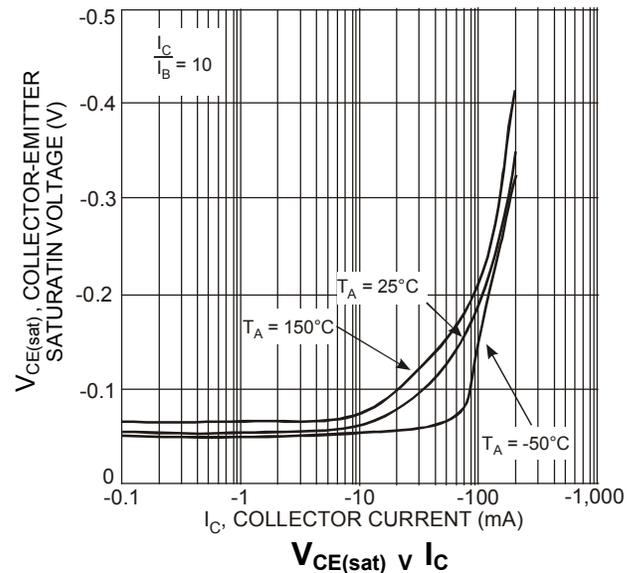
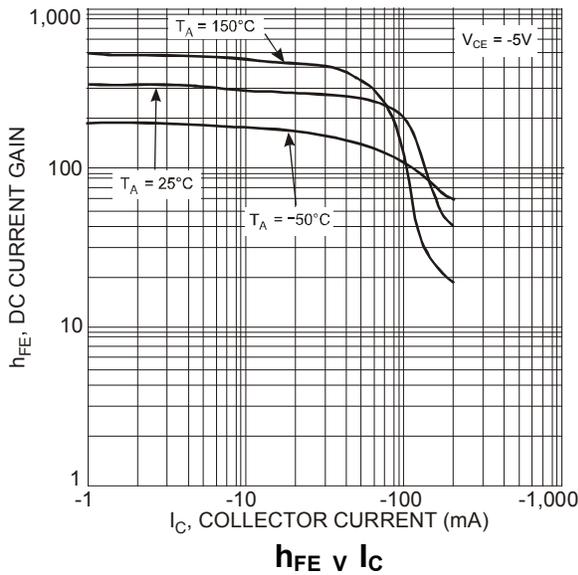


f_T v I_C

Electrical Characteristics: PNP, BC857B Type (Q₂) (@T_A = +25°C unless otherwise specified.)

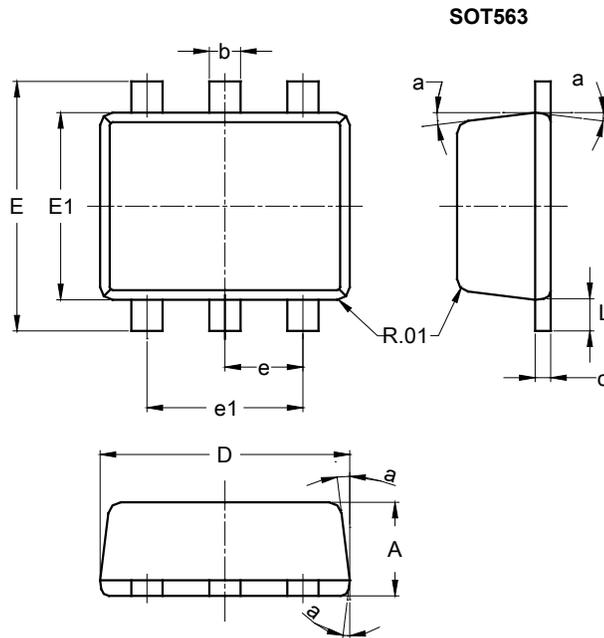
Characteristic (Note 7)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	—	—	V	I _C = -100μA, I _B = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-45	—	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	—	—	V	I _E = -100μA, I _C = 0
DC Current Gain	h _{FE}	220	290	475	—	V _{CE} = -5.0V, I _C = -2.0mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	-75 -250	-300 -650	mV	I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	-700 -850	— -950	mV	I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5.0mA
Base-Emitter Voltage	V _{BE(on)}	-600	-650	-750 -820	mV	V _{CE} = -5.0V, I _C = -2.0mA V _{CE} = -5.0V, I _C = -10mA
Collector Cut Off Current	I _{CBO}	—	—	-15 -4.0	nA μA	V _{CB} = -30V V _{CB} = -30V, T _A = +150°C
Transition frequency	f _T	100	200	—	MHz	V _{CE} = -5.0V, I _C = -10mA, f = 100MHz
Collector-Base Capacitance	C _{cbo}	—	3	4.5	pF	V _{CB} = -10V, f = 1.0MHz

Note: 7. Short duration pulse test used to minimize self-heating effect.



Package Outline Dimensions

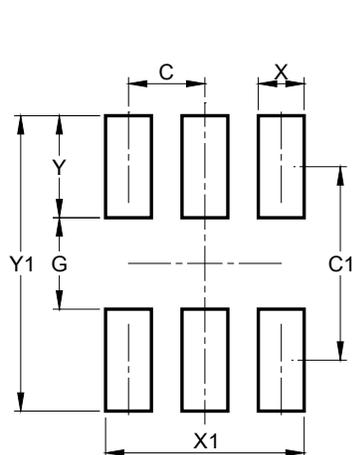
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT563			
Dim	Min	Max	Typ
A	0.55	0.60	0.60
b	0.15	0.30	0.20
c	0.10	0.18	0.11
D	1.50	1.70	1.60
E	1.55	1.70	1.60
E1	1.10	1.25	1.20
e	--	--	0.50
e1	0.90	1.10	1.00
L	0.10	0.30	0.20
a	8°	9°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.500
C1	1.270
G	0.600
X	0.300
X1	1.300
Y	0.670
Y1	1.940

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